

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-5. (canceled)

6. (currently amended) A method for manufacturing a semiconductor device, comprising:

forming an insulating film on a semiconductor substrate, said insulating film comprising at least a high-k insulating film that has higher dielectric constant than that of the silicon oxide film; [[and]]

selectively removing said insulating film via a wet etching with a chemical solution containing an organic solvent as a main component to partially expose said surface of said semiconductor substrate;

before said selectively removing said insulating film via a wet etching, forming a patterned protective film having a predetermined geometry on said insulating film;

selectively removing a part of said high-k insulating film via a dry etching utilizing said protective film as a mask;  
and

removing said protective film.

7-12. (canceled)

13. (original) The method according to claim 6, wherein said organic solvent is a solvent having polar group.

14-18. (canceled)

19. (original) The method according to claim 6, wherein said organic solvent is selected from the group consisting of: isopropyl alcohol; ethylene glycol; 2-heptanone; cyclopentanone; methylethyl ketone; glycol ether; propyleneglycol monomethyl ether; and propyleneglycol monomethyl acetate.

20-23. (canceled)

24. (original) The method according to claim 6, wherein said organic solvent is isopropyl alcohol, and said chemical solution contains not less than 90 % vol. of isopropyl alcohol.

25-31. (canceled)

32. (currently amended) The method according to claim [[31]] 6, wherein in said selectively removing a part of said high-k insulating film via a dry etching, said dry etching is continued to a halfway to the entire thickness of said high-k insulating film.

33. (canceled)

34. (new) A method for manufacturing a semiconductor device, comprising the steps of:

forming an insulating film on a semiconductor substrate, said insulating film comprising at least a high-k insulating film that has higher dielectric constant than that of the silicon oxide film;

selectively removing said insulating film via a wet etching with a chemical solution containing an organic solvent as

a main component to partially expose said surface of said semiconductor substrate;

before said selectively removing said insulating film via a wet etching, forming a patterned protective film having a predetermined geometry on said insulating film; and

selectively removing a part of said high-k insulating film via a dry etching utilizing said protective film as a mask.

35. (new) The method according to claim 34, wherein said organic solvent is a solvent having a polar group.

36. (new) The method according to claim 34, wherein said organic solvent is selected from the group consisting of: isopropyl alcohol; ethylene glycol; 2-heptanone; cyclopentanone; methylethyl ketone; glycol ether; propyleneglycol monomethyl ether; and propyleneglycol monomethyl acetate.

37. (new) The method according to claim 34, wherein said organic solvent is isopropyl alcohol, and said chemical solution contains not less than 90% vol. of isopropyl alcohol.

38. (new) The method according to claim 34, wherein in the step of selectively removing a part of said high-k insulating film via a dry etching, the dry etching is continued to halfway the entire thickness of said high-k insulating film.

39. (new) The method according to claim 34, after the step of selectively removing said insulating film via a wet etching, further comprising the step of rinsing the surface of said semiconductor substrate with an organic solvent, wherein in

selectively removing said insulating film via a wet etching, said chemical solution includes a fluoride-containing compound.

40. (new) A method for manufacturing a semiconductor device, comprising the steps of:

forming an insulating film on a semiconductor substrate, said insulating film comprising at least a high-k insulating film that has higher dielectric constant than that of the silicon oxide film;

selectively removing said insulating film via a wet etching with a chemical solution containing an organic solvent as a main component and a fluoride-containing compound to partially expose said surface of said semiconductor substrate; and

after said selectively removing said insulating film via a wet etching, rinsing the surface of said semiconductor substrate with an organic solvent.

41. (new) The method according to claim 40, wherein in rinsing the surface of said semiconductor substrate, said organic solvent is isopropyl alcohol.

42. (new) The method according to claim 40, wherein said organic solvent is isopropyl alcohol, and said chemical solution contains not less than 90% vol. of isopropyl alcohol.